

Appl. No. 10/613,606

Amdt. dated June 18, 2004

Reply to Office action of March 19, 2004

**Amendments to the Abstract:**

Please replace Abstract with the amended Abstract on the following page:

### ABSTRACT

A new method is provided for the removal of liner oxide from the surface of a gate electrode during the creation of the gate electrode. A layer of gate oxide is formed over the surface of a substrate, a layer of gate electrode such as polyimide is deposited over the layer of gate oxide. The gate electrode is deposited, gate spacers are formed over the liner oxide, exposing surfaces of the liner oxide. The created structure is nitrided by a plasma stream containing  $N_2/H_2$ , reducing the etch rate of the exposed liner oxide. The liner oxide is then removed by applying a wet etch, contact regions to the gate electrode are salicided.